

FLL101ME

October 7, 1993

1. ABSOLUTE MAXIMUM RATINGS (Ambient Temperature $T_a=25^{\circ}\text{C}$) (Standard)

Item	Symbol	Condition	Rating	Unit
Drain-Source Voltage	VDS		15	V
Gate-Source Voltage	VGS		-5	V
Total Power Dissipation	Pt	$T_c=25^{\circ}\text{C}$	4.17	W
Storage Temperature	Tstg		-65 to +175	$^{\circ}\text{C}$
Channel Temperature	Tch		+175	$^{\circ}\text{C}$

2. ELECTRICAL CHARACTERISTICS (Ambient Temperature $T_a=25^{\circ}\text{C}$)

Item	Symbol	Test Conditions	Limit			Unit
			Min.	Typ.	Max.	
Drain Current	IDSS	VDS=5V, VGS=0V	-	300	450	mA
Transconductance	gm	VDS=5V, IDS=200mA	-	150	-	mS
Pinch-off Voltage	Vp	VDS=5V, IDS=15mA	-1.0	-2.0	-3.5	V
Gate-Source Breakdown Voltage	VGSO	IGS=-15uA	-5	-	-	V
Output Power at 1dB G.C.P.	P1dB	VDS=10V	28.5	29.5	-	dBm
Power Gain at 1dB G.C.P.	G1dB	IDS=0.6IDSS	12.5	13.5	-	dB
Power-added Efficiency	Nadd	f=2.3GHz	-	47	-	%
Thermal Resistance	Rth	Channel to Case	-	25	36	$^{\circ}\text{C}/\text{W}$

G.C.P.: Gain Compression Point

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